

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

Listing of Claims:

1. (Currently Amended) A semiconductive glaze product comprising:

a glaze composition and a flux, ~~the glaze composition containing~~including a KNaO-MgO-CaO-Al₂O₃-SiO₂-based base glaze and a metal oxide composition including tin oxide and antimony oxide, in which the ~~wherein~~ relative compositional proportions of the base glaze, as represented by the Seger formula of basic components, mainly include KNaO in a range of 0.1 to 0.4, MgO in a range of 0.2 to 0.6, and CaO in a range of 0.2 to 0.7, are 0.1 to 0.4, 0.2 to 0.6, and balance, respectively, Al₂O₃ in a range of 0.5 to 0.9 and SiO₂ in a range of 4 to 7 and ~~containing a metal oxide composition including tin oxide and antimony oxide,; and~~ a flux in wherein the ~~an~~ amount of the flux is 10 parts by weight or less based on the basis of 100 parts by weight of the glaze composition.

2. (Original) The semiconductive glaze product according to claim 1, wherein the flux is boron oxide.

3. (Cancelled).

4. (Currently Amended) The semiconductive glaze product according to claim 1, wherein ~~the~~ the glaze composition comprises amounts of the 60 to 80 wt% of the base glaze and 20 to 40 wt% of the metal oxide composition ~~contained in the glaze composition are 60 to 80 wt.% and 40 to 20 wt.%, respectively to total 100 wt% of the glaze composition.~~

5. (Currently Amended) The semiconductive glaze product according to claim 1, wherein the metal oxide composition includes 2 to 15 wt% of antimony oxide ~~content of the metal oxide composition is 2 to 15 wt.%.~~

6. (Currently Amended) The semiconductive glaze product according to claim 1, wherein the metal oxide composition ~~contains~~ includes niobium oxide in an amount of 5 wt% or less.

7. (Withdrawn) A method for producing a semiconductive glaze product comprising mixing predetermined amounts of a flux and a glaze composition containing a base glaze and a metal oxide, the flux and the glaze composition serving as raw materials; and adding water to the resultant mixture to thereby form a slurry, wherein particles of the raw materials, mainly the glaze composition and the flux, are reduced in size such that large particles having a size of at least 10 μm account for 15 wt.% or less of the entirety of the particulate raw material mixture.

8. (Withdrawn) The method for producing a semiconductive glaze product according to claim 7, wherein wollastonite is employed as a Ca source.

9. (Previously Presented) An insulator comprising an insulator main body whose surface is coated with a semiconductive glaze product as recited in claim 1.